Microwave Nanosecond Pulse Burnout Properties of GaAs MESFETs (1979 [MWSYM])

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Microwave nsec pulse burnout data have been measured at 9 GHz for three 1 micron gate MESFETs. Values of incident pulse power and absorbed energy required to cause burnout are presented and discussed. Also discussed are the dominant failure modes for the overstressed MESFETs.

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